

<i>Notice of References Cited</i>	Application/Control No. 10/531,391		Applicant(s)/Patent Under Reexamination WATANABE ET AL.	
	Examiner XNNING NIU		Art Unit 2828	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2002/0039374	04-2002	Onomura et al.	372/46
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.